

V60

# Diode Laser Spectroscopy

Fritz Agildere  
fritz.agildere@udo.edu

Amelie Strathmann  
amelie.strathmann@udo.edu

Experiment: April 29, 2024

Submission:

TU Dortmund – Department of Physics

# Contents

<b>1 Objective</b>	<b>2</b>
<b>2 Theory</b>	<b>2</b>
2.1 Historical Background .....	2
2.2 Diode Laser .....	2
2.2.1 Structure and Mode of Operation .....	2
2.2.2 Laser Tuning .....	4
<b>3 Setup</b>	<b>6</b>
<b>4 Procedure</b>	<b>6</b>
<b>5 Results</b>	<b>6</b>
<b>6 Discussion</b>	<b>8</b>
<b>Appendix</b>	<b>9</b>

# 1 Objective

In this experiment, the functioning of a diode laser is considered in order to use it to record different resonance and fluorescence lines of rubidium.

## 2 Theory

The following section explains the theoretical principles of a diode laser.

### 2.1 Historical Background

Before semiconductor lasers were invented, physicists used tunable 'dye' lasers. This worked by the use of a chemical dye as the active medium, i.e the material which produces the laser emission. A fixed-frequency 'pump'-laser is used to create a population inversion. Each individual dye will lase over a limited wavelength range. This means with different dyes it is possible to generate a tunable lasers at basically all near-infrared wavelengths. Dye Lasers have some disadvantages. They are very large, with high costs of purchase and operation.

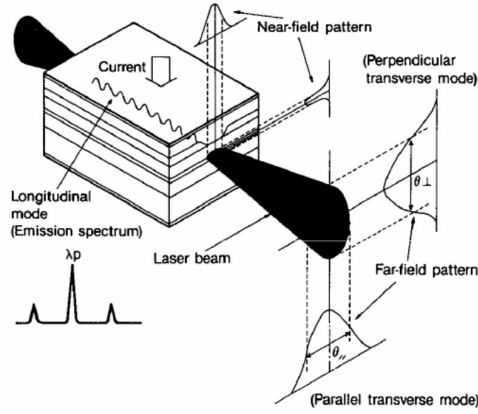
The situation has changed due to the development of the diode laser. These lasers are inexpensive, easy to operate and produce high power.

### 2.2 Diode Laser

The basics of how a diode laser works are explained below.

#### 2.2.1 Structure and Mode of Operation

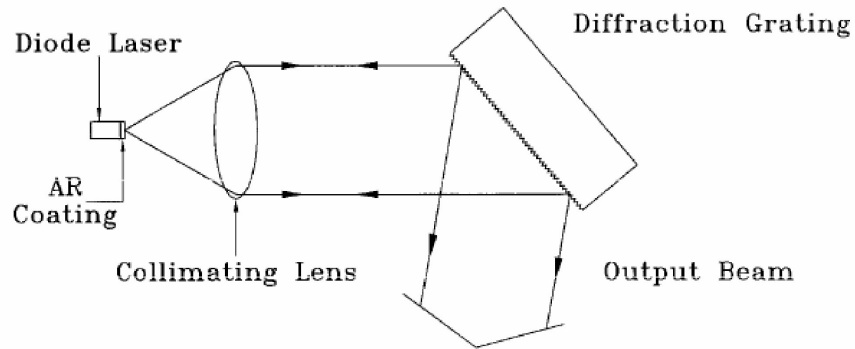
A diode laser is a laser whose light is generated with a laser diode, i.e. with semiconductor materials. An important component is the diode chip which can be seen in figure 1.



**Figure 1:** Schematic view of a laser diode chip.

The chip consists of a p-doped and a n-doped layer. The p-n junction between the layers is the active Medium. An excitation current can be connected to the upper and lower ends of the diode to create electron-hole pairs which recombine in the active layer and emitting light in the process. The current serves as a pump source for the population inversion which occurs in the laser medium. The wavelength of the emitted light is approximately that of the band gap of the semiconductor material. To create a cavity the cleaved facets of the chip act as a partially reflecting mirrors. On this side the light comes out. Standing waves are formed inside the cavity. The leaving light beam is elliptical and strongly divergent due to the rectangular shape of the exit aperture.

The light beam has two unwanted properties which are to be adjusted by an external resonator. On one hand the light beam has a large linewidth therefore it is unusable to examine atomic structures. On the other hand the frequency stability is very sensitive to scattering of the emitted light back into the diode. A Littrow configuration is used in this experiment which is shown in figure 2.



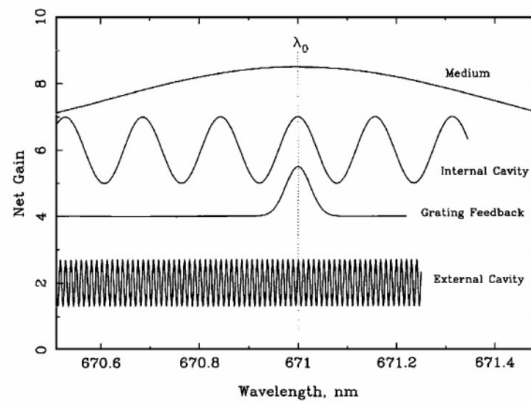
**Figure 2:** Schematic configuration of the diode laser system.

The external cavity is realized with a lens and a diffraction grating. After leaving the inner cavity the light beam hits a lens which collimate the beam. Afterwards the light beam encounters the diffraction grating. Most of the light directly reflected by the grating ( $m = 0$  grating order). About 15% reflects back into the laser ( $m = 1$  grating order). The grating forms the external cavity. This results in a small loss of power, but a much more stable laser beam and a reduced linewidth on  $\Delta\nu \approx 1$  MHz.

### 2.2.2 Laser Tuning

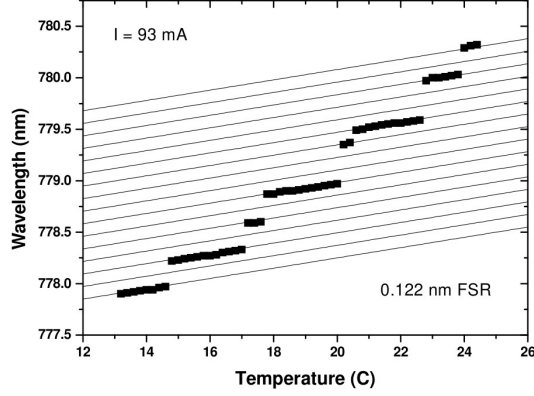
To set up the wavelength of the light emitted by the laser various components must be considered. Therefore the laser output depends for example on modulation of the current, the temperature of the diode and the position of the grating. To understand each component it is important to understand that the laser will tend to lase at the mode frequency with the greatest net gain. As soon as the laser starts lasing in this mode it results a laser with a single-mode output beam. Under real conditions the laser will sometimes lase in two or more modes at the same time. This experiment will concentrate to find a place in parameter space where the laser operates in a single mode.

In Figure 3 the wavelength is plotted as a function of the individual amplification modes. The curves are displaced relative to one another.



**Figure 3:** Schematic of the different contributions to the net gain.

The active medium has a bandgap which depends on the material of the medium. This results in a broad peak in the wavelength distribution of the amplification. The peak depends on the temperature of the material. In the case of rubidium for the resonance the temperature should be set so that the laser operates near 780 nm. Dependence is shown in figure 4.



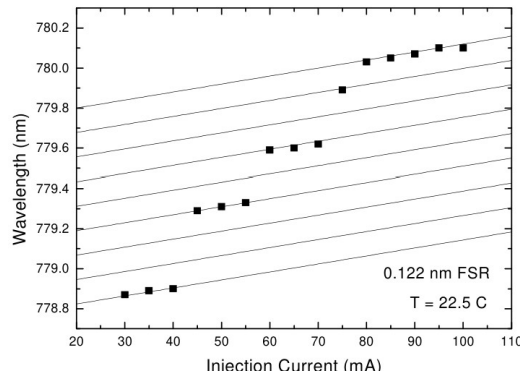
**Figure 4:** Dependence of the wavelength on the temperature of the diode.

It can be seen that the wavelength correlates with the temperature of the diode. That means the rising temperature impacts the Bandgab, which shrinks. Once the medium gain curve is adjusted the curve is so broad that it is unimportant for net gain.

The internal cavity forms a small Fabry-Perot etalon thus a optical cavity with a normal mode structure. As shown in figure 3 the gain function is periodic in frequency, whereby the period is called free spectral range. Which is given by

$$\Delta\nu = \frac{c}{2Ln}. \quad (1)$$

In this equation  $c$  is the speed of light,  $n$  is the index of refraction and  $L$  is the cavity length. For the internal cavity the wavelength of the light depends on the current which is represented in figure 5. The current affects the diode in two ways. First, the diode is heated by the applied current. Second, the current changes the carrier concentration in the active medium.



**Figure 5:** Dependence of the wavelength on the injection current at a fixed temperature.

With a external cavity it is possible that the laser can be made to operate at any wavelength within a reasonably broad range. Since only light from a narrow wavelength band ( $m = 1$  grating order) will be fed back into the laser for a fixed grating, which can be found by

$$\lambda = 2d \sin \theta. \quad (2)$$

The size  $d$  indicates the line spacing of the grating and  $\theta$  is the grating angle. The external cavity ist limited on the one side by the grating and on the oder side by the refelective back faced of the diode. The length of the external cavity is much smaller which results denser peaks in figure 3.

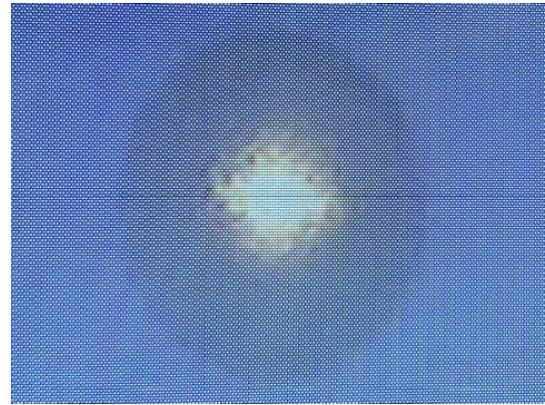
### 3 Setup

### 4 Procedure

### 5 Results



(a) LED regime at  $I = 34.4$  mA.

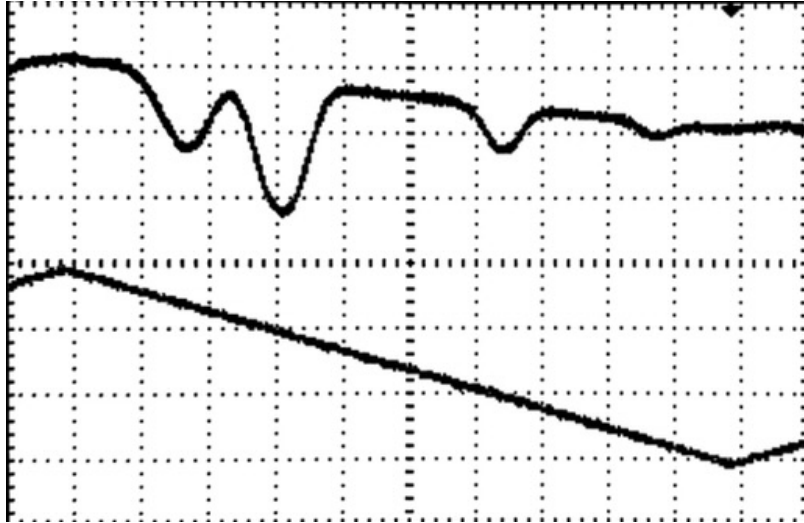


(b) LASER regime at  $I = 34.6$  mA.

**Figure 6:** Comparison of light pattern slightly below and above the chosen threshold current  $I = 34.5$  mA. Notice the diffuse reflection on the left versus the coarse granulation on the right. These distinct appearances are the results from random diffraction of incoherent or coherent waves respectively.

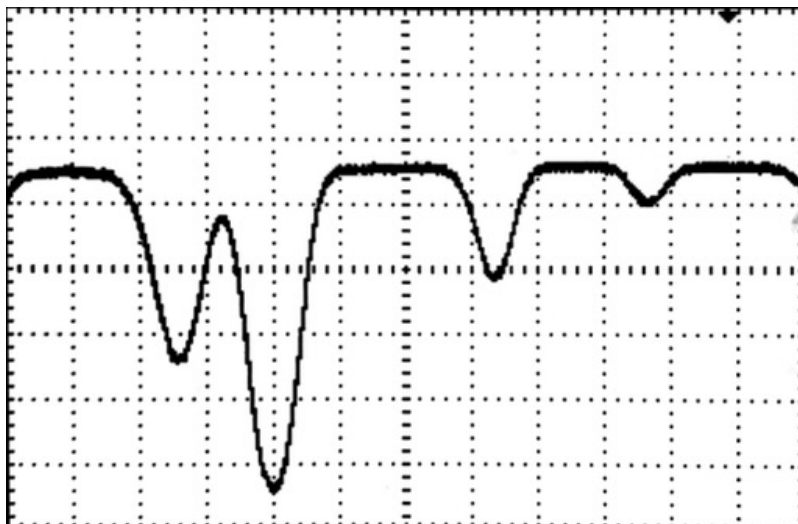


**Figure 7:** Rubidium fluorescence line along the laser beam as seen through the observation window in the vapor cell.



**Figure 8:** Modulated signal without correction (top). Triggered ramp output for laser and piezo stack (bottom). As previously described, the expected linear proportionality between the two currents is clearly visible outside the absorption dips.





**Figure 9:** Spectrum after manual compensation via background subtraction for the scanning current contribution.

## 6 Discussion

## Appendix